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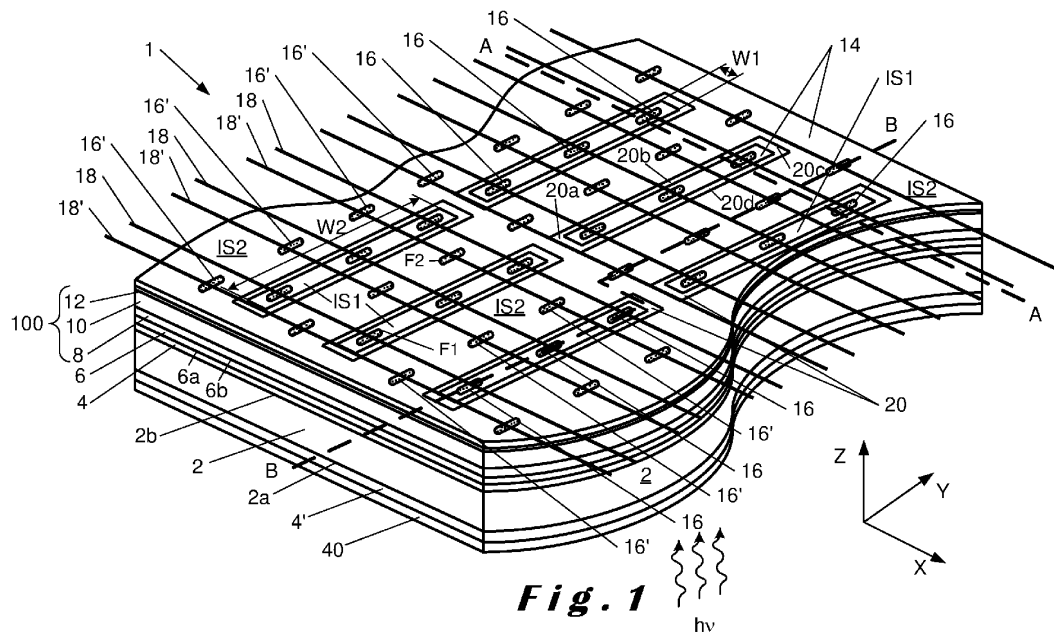
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(54) Title: PHOTOVOLTAIC DEVICE AND METHOD FOR MANUFACTURING THE SAME



(57) Abstract: In the present invention a method to fabricate an interdigitated back contact (IBC) photovoltaic device (1) is disclosed and comprises the steps of providing a substrate (2) of a first-type doping being an n-type or a p-type doping; realizing on a back side (2b) a semiconducting doped structure (6) comprising individual doped layers portions (6') of said first type doping and a semiconducting doped structure (6'') of a second type; realizing a conductive layer (100) on top of the semiconducting structure (6); realizing a patterned isolation resist layer (14) having contact apertures (14b) and isolation apertures (14c) onto said conductive layer (100); further applying a plurality of conductive pads (16, 16') to said contact apertures (14b); and etching the conductive layer (100) up to said second-type doped layer (6'') to realize trenches (20) to electrically separate first type charge collecting structures (F1) from second type charge collecting structures (F2). The invention provides also an interdigitated back contact (IBC) photovoltaic device (1) as manufactured according

WO 2022/084205 A1

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to the disclosed method of fabrication. The invention relates also to a photovoltaic system comprising at least two interdigitated back contact (IBC) photovoltaic devices (1).